PROPERTIES OF SILICON DERIVATIVES OF COBALT, MANGANESE AND IRON CARBONYLS

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Although the first compound to contain a silicon-transition metal bond, Me₃Si-Fe(CO)₂(π -C₅H₅), was synthesized by Piper, Lemal and Wilkinson¹ in 1956, it was not until 1965 with the advent of the work by Chalk and Harrod² and Aylett and Campbell³ on silicon cobalt tetracarbonyls that silicon-transition metal chemistry started developing rapidly. The growth of interest in this area of silicon chemistry has been substantial and since the beginning of 1965 approximately thirty-five publications have appeared on this subject.

In this lecture, time is not, of course, available to discuss all of the recent important and interesting advances in silicon-transition metal chemistry. Our research group has been mainly concerned with the structure, and particularly the chemical properties of silicon derivatives of cobalt, manganese and iron carbonyls in which there is a Si–Co, Si–Mn or Si–Fe bond. This lecture will be limited to these derivatives only. In this respect, it might be noted, that in so far as studies of chemical properties are concerned, most investigations to date have been carried out on compounds containing Si–Co, Si–Mn or Si–Fe bonds.

I. SYNTHESIS

Some of the more common or useful methods for synthesizing silicon derivatives of cobalt, manganese and iron carbonyls are summarized below by means of generalized equations in which X is a halogen and R is a substituent, usually hydrogen or an alkyl or aryl group. The most pertinent references are given in each case.

A. Cobalt Carbonyl Derivatives

(1) $R_3SiX + Co(CO)_4 \rightarrow R_3Si-Co(CO)_4 + X^-$

Reaction occurs under mild conditions.³

(2) $2R_3SiH + Co_2(CO)_8 \rightarrow 2R_3Si-Co(CO)_4 + H_2$

Reaction occurs readily at room temperature.^{2, 4, 5}

(3) $R_3SiH + HCo(CO)_4 \rightarrow R_3Si-Co(CO)_4 + H_2$

Reaction occurs readily in the liquid phase at or below room temperature.4-8

(4) $Co_2(CO)_8 + (CH_2 = CH)_4 Si \text{ or } Ph_4 Si \rightarrow polynuclear products.$

Reaction occurs on refluxing in an appropriate solvent to give species such as $CH_2=CH$ —SiCo₃(CO)₉⁹ and [Co₃(CO)₉Si]₂¹⁰ respectively.

(5) $HCo(PF_3)_4 + Me_3SiNMe_2 \rightarrow Me_3Si-Co(PF_3)_4 + Me_2NH$

The characterization of the Me₃Si— $Co(PF_3)_4$ is incomplete and it may well be complexed with the liberated amine.¹¹

B. Manganese Carbonyl Derivatives

(1) $R_3SiX + Mn(CO)_5 \rightarrow R_3Si - Mn(CO)_5 + X^-$

Reaction proceeds under mild conditions.^{12, 13}

(2) $R_3SiH + HMn(CO)_5 \rightarrow R_3Si-Mn(CO)_5 + H_2$

Reaction occurs at 130-135°.14

(3) $Mn_2(CO)_{10} + 2R_3SiH \rightarrow 2R_3Si-Mn(CO)_5 + H_2$

On heating the reactants in the 100–180° range, the reaction proceeds readily¹⁵, ¹⁶.

C. Iron Carbonyl Derivatives

(1) $2R_3SiX + Fe(CO)_4^{-2} \rightarrow (R_3Si)_2Fe(CO)_4 + 2X^{-1}$

This type of reaction proceeds readily and it has also been used for attaching the $-Fe(CO)_2(\pi-C_5H_5)$ group to silicon^{1, 17, 18}.

(2) $6R_3SiH + Fe_3(CO)_{12} \rightarrow 3(R_3Si)_2Fe(CO)_4 + 3H_2$

This type of reaction occurs on heating the reagents in the 80–180° range^{16, 19}. Cyclic species¹⁶ and compounds such as $(SiCl_3)_2FeH(CO)$ $(\pi-C_5H_5)^{20}$ have also been isolated when $Fe(CO)_5$ or $[(\pi-C_5H_5)Fe(CO)]_2$ respectively are used in place of the $Fe_3(CO)_{12}$.

D. Compounds Synthesized in this Study

The compounds Me₃Si-Co(CO)₄, MeSiH₂—Co(CO)₄ and F₃Si-Co(CO)₄ were synthesized in good yields from the corresponding silane and Co₂(CO)₈ in the absence of solvent at room temperature^{5-8, 21}. The species MeSiF₂-Co(CO)₄ was prepared by fluorinating MeSiH₂-Co(CO)₄ with PF₅ at room temperature.^{21, 22}

The reaction of $HCo(CO)_4$ with silanes such as Me₃SiH, F₃SiH and Cl₃SiH etc. proceeded very rapidly at or below room temperature to give the corresponding silicon cobalt tetracarbonyls^{4, 5, 8, 21}. In the case of

Me₃SiH, which was the only compound studied under these conditions, no interaction occurred in the gas phase at room temperature during several hours.⁷ No reaction took place between Me₃SiH or Cl₃SiH and HCo(CO)₂(PF₃)₂ either in solution or in the gas phase at room temperature²¹. It is interesting that this type of reaction could readily be extended to Me₂AsH. Rapid reaction occurred at or below room temperature, viz^{5} , ⁷.

$xMe_{2}AsH + xHCo(CO)_{4} \rightarrow [Me_{2}As-Co(CO)_{3}]_{x} + xCO + xH_{2}$

Since $HCo(CO)_4$ can be isolated from the reaction of a silane with $Co_2(CO)_8$, viz.^{4-8, 21}

$$R_3SiH + Co_2(CO)_8 \rightarrow R_3Si-Co(CO)_4 + HCo(CO)_4$$

the overall reaction between R_3SiH and $Co_2(CO)_8$ may proceed via the intermediate formation of $HCo(CO)_4^{4, 5, 7}$ which then reacts with another molecule of R_3SiH , or partial decomposition of $HCo(CO)_4$ might occur, *viz*.

$$2HCo(CO)_4 \rightarrow Co_2(CO)_8 + H_2$$

the $Co_2(CO)_8$ then reacting with another molecule of R_3SiH . It is likely that both types of reaction sequences occur depending on the silane used.⁴

The manganese derivative, Me₃Si-Mn(CO)₅, was prepared in 68 per cent yield from the reaction of Me₃SiCl with NaMn(CO)₅ at room temperature and 70 per cent yield by heating Me₃SiH with Mn₂(CO)₁₀ at 130° for 48 hours¹⁴. A reaction took place at 130–135° during one day between Me₃SiH and HMn(CO)₅ giving 23 per cent yields of this compound,¹⁴ viz.

$$Me_3SiH + HMn(CO)_5 \rightarrow Me_3Si-Mn(CO)_5 + H_2.$$

The Me₃Si–Fe(CO)₂(π -C₅H₅) was prepared fromNaFe(CO₂)(π -C₅H₅) and Me₃SiCl according to the method of Piper *et al.*¹

II. THERMOCHEMICAL DATA

Mass spectroscopic appearance potential studies on $F_3Si-Co(CO)_4$ and $MeSiF_2-Co(CO)_4$ gave Si-Co bond dissociation energies of 105 ± 12^{23} and 124 ± 12^{24} kcal/mole respectively[†]. The corresponding standard heats of formation are -489.7 ± 10 and -433 ± 12 kcal/mole respectively^{23, 24}. Because of the possibility of excess kinetic energy in the ion fragments, the bond dissociation energies should be regarded as maximum values and the heats of formation as minimum values. Nevertheless, these data indicate that the Si—Co bond is rather strong and it may be compared, for example, with the value of 82 ± 2 kcal/mole reported for the Si—Cl bond dissociation energy in Me₃SiCl.²⁵

III. STRUCTURE

As is well known, some silicon compounds have structures which differ considerably from those of analogous carbon compounds; trimethylamine for example, is a pyrimidal molecule whereas the nitrogen and three silicon atoms in $(SiH_3)_3N$ are coplanar.²⁶ It is therefore of interest to compare the structures of analogous carbon- and silicon-transition metal derivatives where the appropriate data are available.

 † If a value of -164 kcal/mole is used for \triangle H^e_f of Co(CO)₄ (see Bidinosti and McIntyre⁷²) these values become 73 and 95 kcal/mole, respectively.

A. R_3Si —Co(CO)₄

Infrared studies in the CO stretching region of compounds of the type $R_3Si-Co(CO)_4$ [$R_3Si-H_3Si-R_3Si-$

It should be noted that in so far as comparable data are available, the carbon and silicon cobalt tetracarbonyls have similar structures. Thus the infrared spectra of H_3C — $Co(CO)_{4,32,33}$ F_3C — $Co(CO)_{4^{34}}$, and Me_3C — $Co(CO)_{4^{19}}$ in the CO stretching region are consistent with axially substituted trigonal bipyrimidal molecules.

B. $R_3Si - Mn(CO)_5$

Infrared studies in the CO stretching region of compounds of the type R_3Si — $Mn(CO)_5$ (R_3Si — = Me_3Si — (gas phase and solution)^{14} and R_3Si — $^{15, 16, 29, 30} =$ Ph_3Si — Me_3Si —, Cl_3Si — (solution)) are consistent with an octahedral



Figure 1. Structure of: (a) R-Co(CO)₄, (b) R-Mn(CO)₅ where R is hydrogen or a group IV substituent.

conformation about the manganese. This type of configuration is supported by an X-ray single crystal study of Me₃Si—Mn(CO)₅³⁶. The simple alkyl derivatives, R₃C—M_n(Co₅, (R = H, F, *etc.*), have similar structures.³⁵

C. $(R_3Si)_2$ Fe(CO)₄ and R_3Si —Fe(CO₂)(π -C₅H₅)

Infrared studies in the CO stretching region of $(SiH_3)_2Fe(CO)_4^{17}$, $(Et_3Si)_2Fe(CO)_4^{19}$ and $SiH_3(H)Fe(CO)_4^{17}$ are consistent with octahedral

structures in which the substituent groups are *cis* to each other. It is interesting to note that the isomeric *cis* and *trans* forms of $(SiCl_3)_2Fe(CO)_4$ have been isolated.¹⁹ It might be noted that in H₂Fe(CO)₄³⁷ and in perfluoroalkyl derivatives such as $(C_2F_5)_2Fe(CO)_4^{34}$ the substituents are *cis* to each other although it has been pointed out that the presence of a *trans* isomer in the latter compound cannot definitely be ruled out.³⁴

It is probable that the structures of compounds such as Me₃Si-Fe(CO)₂ $(\pi$ -C₅H₅)¹, Cl₃Si-Fe(CO)₂ $(\pi$ -C₅H₅)¹⁶ and MeCl₂Si-Fe(CO)₂ $(\pi$ -C₅H₅ can be regarded, at least to a first approximation, as being derived from an octahedral iron atom with three coordination positions being occupied by the C₅H₅ ring, the other three positions being occupied by the two carbonyl groups and by the silicon group. It is interesting to note that the infrared spectrum of MeSiCl₂-Fe(CO)₂ $(\pi$ -C₅H₅) strongly suggests the presence of two conformational, isomeric forms for the molecule¹⁶.

IV. BONDING

A. $(d \rightarrow d)\pi$ Bonding Between a Transition Metal and Silicon

A number of infrared studies of the CO stretching region of silicon and other Group IV transition metal carbonyls have given evidence for the possible presence of partial $(d \rightarrow d)\pi$ double bond character in the Group IV transition metal bond^{19, 21, 27, 29,38, 39}. Certain of these studies have been correlated with dipole moment measurements¹⁹. This interaction is depicted diagrammatically in Figure 2(a) for R₃Si—Mn(CO)₅ where, for simplicity, the manganese atom and the four equatorial CO groups are shown as being coplanar. Only the $(d_{zx} \rightarrow d_{zx})\pi$ interaction is depicted. An analogous $(d_{yz} \rightarrow d_{yz})\pi$ interaction involving the other two equatorial CO groups would also be present. This type of bonding therefore involves an overlap of filled manganese 3d orbitals with the empty silicon 3d orbitals. It can be seen that this interaction might be expected to affect the extent of interaction of the type shown in Figure 2(b) between the manganese and the empty antibonding π orbitals of the carbonyl groups and hence to affect the CO stretching frequencies. Analogous types of interactions can be postulated for the cobalt and iron carbonyl derivatives.

It is of interest to examine some of the X-ray data available for such compounds in order to ascertain whether or not they are consistent with the $(d \rightarrow d)\pi$ bonding hypothesis. A Si—Co bond length of 2.254 ± 0.003 Å has been determined from a single crystal X-ray study of Cl₃Si—Co(CO)₄³¹. In view of the uncertainty in assigning an unequivocal value for the covalent radius of cobalt in a compound such as this, considerable care must be exercised in interpreting this datum. However, it appears likely that the covalent radius of cobalt is not less than 1.22Å in view of the 1.243Å covalent radius reported for cobalt in CoH⁴⁰ and the 1.32Å value found in the penta co-ordinate cobalt compound, Co[Me₂N(CH₂)₂NMe₂[CH₂)₂NMe₂]Cl₂.⁴⁰ A range of values, 1.22 to 1.32Å, for this radius has been found in fifteen assorted cobalt carbonyls⁴¹.

If the radius for silicon of 1.15\AA from Cl_3Si — SiCl_3^{42} is taken, this then gives a minimum calculated distance for a single Si—Co bond of 2.37\AA . The fact that this calculated value is significantly more (0.12\AA) than the

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experimental Si—Co bond length is certainly consistent with partial $(d \rightarrow d) \pi$ double bond character in this linkage.

A Si—Mn bond length of 2.497 ± 0.005 Å has been determined from a single crystal X-ray study of Me₃Si—Mn(CO)₅³⁶. The calculated Si—Mn single bond length using a value of 1.46Å for the covalent radius of Mn as recommended by Doedens and Dahl⁴³ and a value of 1.17Å for the radius of silicon as determined from Me₃Si—SiMe₃⁴⁴ is 2.63Å. The fact that this value is larger (by 0.13Å) than the calculated Si—Mn single bond radius



Figure 2. Schematic representation of some of the possible bonding interactions in $R_3Si-Mn(CO)_5$. (A sideways view along the XY plane which is represented as containing the Mn and the four equatorial CO groups, two of which are shown, is depicted).

is also consistent with partial $(d \rightarrow d)\pi$ double bond character in this linkage.

Using this same value for the radius of manganese and a value of 1.39Å for the radius of tin, as determined from $(Ph_2Sn_6)^{45}$, a similar difference between calculated and experimental Sn—Mn bond lengths can be observed in a

number of compounds, viz., Ph₃Sn—Mn(CO)₅⁴⁶ (D_{Sn-Mn} experimental, 2.674 ± 0.004 Å; calculated 2.85Å); trans-Ph₃Sn—Mn(CO)₄ PPh₃⁴⁷ (D_{Sn-Mn} experimental, 2.627 ± 0.01 Å); Me₃Sn—Mn(CO)₅⁴⁸(D_{Sn-Mn} experimental, 2.674Å). The transition metal-carbon bond lengths for the equatorial and axial CO groups in the above compounds are either essentially identical or very nearly so. It might be noted, for comparative purposes, that the difference in C—C distances between a carbon–carbon single bond and a carbon–carbon double bond is approximately 0.2Å. The percentage shortening is, of course, considerably greater in the carbon–carbon linkage than in the bonds described above.

It appears unlikely that the amount of ionic character in these linkages would cause the observed shortenings. Thus the Allred and Rochow⁴⁹ electronegativities for these elements are very similar: Si = 1.74, Sn = 1.72, Co = 1.70 and Mn = 1.60.

It should be stressed that the apparent agreement of these bond length data with the $(d \rightarrow d)\pi$ bonding concept suggested from infrared studies may be completely fortuitious since the whole argument is especially dependent on the assignment of an appropriate radius to Co and Mn.

B. $(p \rightarrow d)\pi$ Bonding between axial CO groups and silicon

In discussing interactions other than that of the sigma bond between a Group IV element and a transition metal having attached carbonyl groups, it is of interest to consider whether there is any experimental evidence which is at least qualitatively consistent with a direct "across-space" $(p \rightarrow d)\pi$ interaction between the equatorial CO groups and the Group IV element. In the parent compound, $HCo(CO)_4$, from which the Group IV cobalt tetracarbonyls may be considered be derived, electron diffraction⁵⁰ and (vapour phase) infrared⁵¹ data show that the molecule may be regarded as a trigonal bipyrimid with the hydrogen in an axial position and the equatorial CO groups raised towards the hydrogen such that the H-Co-CO_(eq.) angle is approx. 71° (see Figure 1a). A distortion in this direction might be expected from simple steric considerations involving the axial hydrogen atom and axial CO group. However, molecular orbital calculations^{37,51-54} suggest there may be a strong bonding interaction between the hydrogen 1s orbital and the equatorial CO groups. The question arises whether a somewhat analogous interaction, but involving instead the *d* orbitals of the substituent, exsists in the Group IV derivatives of HCo(CO)₄, and indeed in Group IV derivatives of other transition metal carbonyls.

From simple steric considerations alone, one might expect to find that the equatorial CO groups would be bent *away* from the large Group IV substituent towards the smaller axial CO group *trans* to it. (See also note 1 added in proof on p. 448) Thus, the R_3M —Co—CO_(eq.) angle or the R_3M —Mn—CO_(eq.) angle (M = Si, Ge, Sn, Pb) would be greater than 90°, e.g. (90 + α)°. However, experimentally, in those compounds investigated to date, the axial CO groups are bent *towards* the larger Group IV substituent and the above angle is, therefore (90 - β)° where β is the angle by which the equatorial carbonyl groups are raised above the plane containing the transition metal. Thus the distortion from the angle expected *only on the basis of simple steric effects* is ($\alpha + \beta$)° (see Figure 1). The average value

of the R₃M—M'—CO_(eq.) angle (M' = Co, Mn) within a given compound is: Cl₃Si—Co(CO)₄ (85·2°)³¹, Me₃Si—Mn(CO)₅ (84·5°)³⁶, Me₃Sn—Mn(CO)₅ (84·3°)⁴⁸, Ph₃Sn—Mn(CO)₅ (86·7°)⁴⁶, *trans*-Ph₃Sn—Mn(CO)₄(PPh₃) (85·7°)⁴⁷. The distortions for these compounds are therefore, since a cannot be evaluated, approx. $\geq 4\cdot8^\circ$, $\geq 5\cdot5^\circ$, $\geq 5\cdot7^\circ$, $\geq 3\cdot3^\circ$ and $\geq 4\cdot3^\circ$, respectively. Even in Ph₃PAu—Co(CO)₄ the equatorial CO groups are displaced towards the gold⁵⁵, possibly by an involving the gold 6d orbitals.

Three possible causes for these distortions are (i) intermolecular interactions (distortions) in the crystal lattice, (ii) repulsion of the equatorial CO groups by electron pairs associated with the carbon of the axial CO group and by related effects, 56 and (iii) $(p \rightarrow d)\pi$ bonding interaction somewhat analogous to that postulated in HCo(CO)4, involving instead, the d orbitals of the silicon or tin and the p orbitals of appropriate symmetry on the equatorial CO groups. The magnitudes of the distortion angles are probably greater than that expected on the basis of lattice distortion effects alone, although gas phase structural studies of compounds of appropriate volatility would be most useful in determining the importance of this effect. (see also Note 2 added in proof on p. 448) The fact that the distortion angle is not changed significantly when anaxial CO group in Ph₃Sn-Mn(CO)₅ is replaced by a Ph₃P group suggests that distortion by lone, or π -bonding electron pairs associated with the carbon of the axial CO group may not be an important factor, since the phosphorus of the Ph_3P has no such electrons.

At least in so far as orbital symmetry is concerned, a direct $(p \rightarrow d)\pi$ interaction between the equatorial CO p_2 orbitals and the Group IV element is possible. This is illustrated diagrammatically in Figure 2 (c) using R_3Si — $Mn(CO)_5$ as an example. It might be noted that in $Cl_3Si-Co(CO)_4^{31}$, for example, the average Si.....C intramolecular distance (2.75Å) is less than the sum of the Van der Waals radii of silicon and carbon (3.54Å) but is greater than the sum of the covalent radii of these atoms (1.94Å). These data, although consistent with a direct Si......C interaction, cannot be regarded as supporting evidence for such an interaction since atoms which are attached to the same central element frequently approach closer to each other than the sum of their Van der Waals radii. According to this $(p \rightarrow d)\pi$ concept, the similarity of the distortion angles in Ph₃Sn— Mn(CO)₅ and trans-Ph₃Sn-Mn(CO)₄(PPh₃) would imply that the 5d orbitals of the tin make a better overlap with the p orbitals of the equatorial CO groups than do the 3d orbitals of the phosphorus. X-ray data on nonfluorinated⁵⁷ alkyl or aryl cobalt and maganese carbonyls of these types would be most useful in determining the importance or non-importance of this type of interaction. The distortions could well be due to a combination of the three effects listed above, or, of course, to some completely different effect. It might be noted that during recent years several brief comments have appeared in the literature suggesting the possible existence of some bonding between silicon and an atom (having lone pairs of electrons) from which it is separated by a CH₂ group. Such bonding interactions, as postulated for example, in Me₃Si-CH₂-O-Me⁵⁸, show some resemblance to the type described above. It is here suggested that, at least a portion of the interaction presently ascribed to $(d \rightarrow d)\pi$ bonding between the Group IV

element and the transition metal to which it is attached, may be due to a direct interaction between the d orbital of the Group IV element and the equatorial CO groups.

V. THERMAL STABILITY

There seems little doubt that at least non-fluorinated alkyl silicon derivatives of cobalt, manganese and iron carbonyls are more thermally stable *in vacuo* than their carbon analoguse, where these are known. Thus, although CH₃Co(CO)₄ decomposes fairly rapidly above -30° ⁵⁹, 30 per cent of a sample of H₃Si—Co(CO)₄ was recovered after heating at 100° for half an hour³.

Tertiary alkyl transition metal carbonyls are either very unstable thermally or have defied preparation. They have a very pronounced tendency to decompose to give olefin and transition metal hydride, *e.g.*

 $(Me_3C)_3C \longrightarrow M(CO)_x \longrightarrow Me_2C = CH_2 + HM(CO)_x$

It should be noted however, that the infrared spectrum of Me₃C—Co(CO)₄ has recently been studied¹⁹ but that this compound is apparently very unstable⁶⁰. Little meaningful comparative information concerning the thermal stability of perfluoroalkyl cobalt carbonyls is available, although they apparently have greater thermal stability than the non-fluorinated species. Thus, F_3C —Co(CO)₄ and C_2F_5 —Co(CO)₄ can be distilled unchanged at their boiling points (91° and 110°, respectively)⁶¹.

When silicon cobalt carbonyls are heated *in vacuo*, the thermal decomposition products are found to vary greatly according to the substituents on silicon. Thus, H_3Si — $Co(CO)_4$ gives some SiH₄ and $HCo(CO)_4^3$ and although Ph₃Si— $Co(CO)_4$ yields Ph₆Si₂ on pyrolysis, Et₃Si— $Co(CO)_4$ yields (Et₃Si)₂O at 190°, as the main silicon-containing product⁴. In preliminary experiments, it has been found^{7,62} that appreciable quantities of Me₃Si— $Co(CO)_4$ remain even after it has been heated at 150° for several hours *in vacuo*. Approximately 70 per cent of the Me₃Si-groups were recovered as (Me₃Si)₂O after twenty hours at this temperature. It is perhaps fortuitous that the gross composition of the residue corresponds rather closely to R— $Co_3(CO)_9$, (R = Me₃SiC =),⁷ viz.,

$$3Me_{3}Si-Co(CO)_{4} \rightarrow Me_{3}SiC \equiv Co_{3}(CO)_{9} + (Me_{3}Si)_{2}O + 2CO$$

which is analogous to known compounds where $R = CH_2 = CHSi \equiv 9$, $H_3CC \equiv ^{41}$. It is often noted that a sample of Me₃Si—Co(CO)₄, which is an essentially colourless solid at room temperature, liberates small quantities of (Me₃Si)₂O within approximately an hour and changes to pink or red. However, after three months *in vacuo* at room temperature, in normal laboratory lighting, 87 per cent of a sample was recovered unchanged⁷.

Both $MeSiH_2$ — $Co(CO)_4$ and $MeSiF_2$ — $Co(CO)_4$ show reasonably good thermal stability²¹ although decomposition always appears to proceed fairly rapidly at first and then to slow down. Thus, after five days at room temperature, followed by one day at 61°, a sample of $MeSiH_2$ — $Co(CO)_4$ (neat liquid) showed relatively little decomposition, although small amounts of $(MeSiH_2)_2O$ and $HCo(CO)_4$ were formed²¹. Approximately 50 per cent of a sample of $MeSiF_2$ — $Co(CO)_4$ (neat liquid) had decomposed after twelve hours at room temperature to yield $(MeSiF_2)_2O$ as the only isolable silicon-containing decomposition product²¹.

The fluorinated compound, F_3Si —Co(CO)₄ (neat liquid), undergoes complete decomposition during eighteen hours at room temperature⁸. The decomposition may be represented by the equation:

$$8\mathrm{SiF}_{3}\mathrm{Co}(\mathrm{CO})_{4} \rightarrow 6\mathrm{SiF}_{4} + 4\mathrm{CO} + 2\mathrm{Si} + \mathrm{Co}_{4}(\mathrm{CO})_{12} + \mathrm{Co}_{2}(\mathrm{CO})_{8}$$

All the fluorine appears as SiF₄⁸. No (SiF₃)₂O or Si₂F₆ was formed.

It may be concluded that the major silicon-containing thermal decomposition product of silicon cobalt tetracarbonyls varies greatly according to the substituent on the silicon and the silicon may appear as a silane, disilane or disiloxane, depending on the nature of the substituent.

Hydrides such as $HMn(CO)_5$ and organic derivatives such as $MeMn(CO)_5$ are generally considerably more stable thermally than the analogous $-Co(CO)_4$ species, although $Me_3C-Mn(CO)_5$ has never been isolated. This is reflected in the greater thermal stability of $Me_3Si-Mn(CO)_5$ as compared to $Me_3Si-Co(CO)_4$. Thus, a sample of $Me_3Si-Mn(CO)_5$ (neat liquid) was recovered almost quantitatively after heating at 160° in vacuo for two days¹⁴. Only traces of $(Me_3Si)_2O$ and Me_3SiH were liberated¹⁴. The parent silicon compound, $H_3Si-Mn(CO)_5$, can be stored in an evacuated tube for long periods at room temperature without decomposition¹³.

Although Me₂Fe(CO)₄ does not appear to have been synthesized, (SiH₃)₂Fe(CO)₄ does not, apparently, decompose rapidly below 110°. ¹⁷ The decomposition products include the interesting species H₃Si(H)Fe(CO)₄ and SiH₄¹⁷. The compound Me₃Si—Fe(CO)₂(π -C₅H₅) is also remarkably stable when heated *in vacuo*⁶³. No decomposition occurred during one hour at 160° but some (Me₃Si)₂O was evolved after an hour at 200°.

It has been suggested that the greater thermal stability of silicon cobalt carbonyls as compared to the analogous carbon compounds (where known) may be due to the presence of partial $(d \rightarrow d)\pi$ double bond character in the silicon-transition element bond^{2,3}. Although this may be true, at least in the case of Me₃Si- derivatives, it appears that the greater stability of the silicon compounds could be due to the small tendency of silicon to form $(p-p)\pi$ double bonds with carbon. It is interesting to note that those silicon compounds which have, in general, a greater thermal stability than analogous carbon compounds, e.g. Me_3Si-M (M = transition metal), $R_2Si(OH)_2$, and R₂Si(NH₂)₂ give thermal decomposition products which differ considerably in type from those of their carbon analogues. In all cases, the carbon compounds give species containing $(p-p)\pi$ double bonds, viz., Me₂C=CH, $R_2C=O$ and $R_2C=NH$, respectively. It is therefore not unlikely that the transition state for decomposition of the carbon compounds involves somewhere a partial $(p-p)\pi$ double bond between carbon and carbon, carbon and oxygen or carbon and nitrogen, respectively. Since the formation of a partial $(p-p)\pi$ double bond between silicon and carbon, silicon and oxygen or silicon and nitrogen is much less likely, this type of reaction mechanism is less probable for the silicon compounds and hence the silicon compounds probably undergo thermal decomposition by a different, higher activation energy process.

VI. OXIDATIVE STABILITY (TO OXYGEN)

Very few studies of the reaction of *dry* oxygen with silicon derivatives of the transition metals have been performed. The compound $(SiH_3)_2Fe(CO)_4$ explodes in air¹⁷ but this violent oxidation is presumably related to the presence of the Si—H bonds.

After Me₃Si—Co(CO)₄ had been exposed to dry oxygen at 1 atm. pressure at room temperature for forty-five minutes, 81 per cent of the Me₃Si- groups were liberated as Me₃Si)₂O. The reaction was exothermic⁶⁴. The compound, Me₃Si—Fe(CO)₂(π -C₅H₅) is very much less reactive. Thus, after ninety-six hours exposure to 0.7 atm. pressure of oxygen, 70 per cent of the compound was recovered unchanged, and some (Me₃Si)₂O was evolved⁶³.

VII. CLEAVAGE OF THE SILICON-TRANSITION METAL BOND

It is convenient to divide the treatment of this topic into several categories, depending on the type of reagent employed.

A. By Protonic Reagents

The Si—Co bond in R_3Si —Co(CO)₄ (R = H, Me) is hydrolytically unstable³ and it is cleaved at a rapid but measurable rate at or below room temperature on mixing the compounds with water^{3,5,7}, viz.,

 $2R_3Si-Co(CO)_4 + H_2O \rightarrow (R_3Si)_2O + 2HCo(CO)_4$

When Me_3Si — $Co(CO)_4$ was held with excess water for fifteen minutes at room temperature, 58 per cent yields of $(Me_3Si)_2O$ were obtained; but hydrolysis was quantitative after two hours. If the reaction had been permitted to occur in a homogeneous liquid phase, hydrolysis might well have proceeded very much more rapidly.

When solid Me_3Si — $Mn(CO)_5$ was permitted to stand with excess water for twenty-four hours at room temperature, 80 per cent of the compound was recovered unchanged¹⁴. From the products obtained it was evident that some hydrolysis had taken place:

 $2Me_{3}Si-Mn(CO)_{5} + H_{2}O \rightarrow (Me_{3}Si)_{2}O + 2HMn(CO)_{5}$

However, the apparent hydrolytic stability is presumably due to the fact that solid $Me_3Si-Mn(CO)_5$ is not wetted by water and when an ethereal solution of the compound was treated with excess water only 9 per cent of the compound was recovered unchanged after five minutes at room temperature; longer reaction times resulted in complete hydrolysis and essentially quantitative recovery of $(Me_3Si)_2O$ and $HMn(CO)_5$.¹⁴

The Si—Fe bond is remarkably resistant to hydrolysis. The parent compound, $(SiH_3)_2Fe(CO)_4$ is reported to react quite slowly with water vapour¹⁷. Solid Me₃Si—Fe(CO)₂(π -C₅H₅) undergoes no reaction whatsoever with liquid water during one day at room temperature⁶³. Even when its ethereal solution was treated with excess water for one hour at room temperature, the Me₃Si—Fe(CO)₂(π -C₅H₅) was recovered quantitatively⁶³. This information indicates that the Si—Fe bond is considerably more stable hydrolytically than the Si—Co and Si—Mn bonds in carbonyl species.

Methanolysis of the Si—Co and Si—Mn bonds in Me₃Si—Co(CO)₄ and Me₃Si—Mn(CO)₅ occurs rapidly in homogeneous medium at room temperature. Quantitative yields of Me₃SiOMe were obtained from Me₃Si— $Co(CO)_4$ after forty-five minutes^{5,7}. Fourteen percent of a sample of Me₃Si— Mn(CO)₅ was recovered unchanged from its solution in methanol after five minutes; essentially quantitative yields of Me₃SiOMe were obtained¹⁴.

Although gaseous hydrogen chloride readily cleaves the Si—Co bond in H_3Si —Co(CO)₄³, viz.,

$$H_3Si - Co(CO)_4 + HCl \rightarrow SiH_3Cl + HCo(CO)_4$$

it does not cleave the Si—Mn bond in H_3Si —Mn(CO)₅ either at room temperature or at 75° ¹³. The Si—Fe bonds in $(SiH_3)_2Fe(CO)_4$ also are not readily cleaved by hydrogen chloride. After ten minutes at 40° only 9 per cent of the Si—Fe bonds were broken, (in a stepwise manner), to yield $H_3Si(H)Fe(CO)_4$ and $H_2Fe(CO)_4^{17}$, viz.,

$$\begin{split} (H_3Si)_2Fe(CO)_4 + HCl &\rightarrow H_3Si(H)Fe(CO)_4 + SiH_3Cl \\ H_3Si(H)Fe(CO)_4 + HCl &\rightarrow H_2Fe(CO)_4 + SiH_3Cl \end{split}$$

The Si—Co and Si—Mn bonds are also cleaved readily at, or below room temperature by N—H bonds to give a mixture of products^{7,13}. The chief primary reaction appears to follow the course:

$$R_3Si - M(CO)_x + R'_2N - H \rightarrow R_3Si - NR'_2 + HM(CO)_x$$

where R = H, Me; R' = H, Me; M = Co, Mn. In the reaction between Me₃Si—Co(CO)₄ and Me₂NH, some of the Me₂NH was apparently consumed to form the adduct, Me₃SiCo(CO)₄. Me₂NH. (See Section VII, C)⁷. A clean cut reaction occurred between H₃Si—Mn(CO)₅ and NH₃¹⁷:

 $2H_{3}Si - Mn(CO)_{5} + NH_{3} \rightarrow 2HMn(CO)_{5} + (SiH_{3})_{2}NH$

In the analogous reaction with H_3Si —Co(CO)₄, a number of products, including SiH₄ and (SiH₃)₃N were obtained¹³. The more complex nature of this reaction is believed to be due to the greater acid strength of HCo(CO)₄ as compared to HMn(CO)₅. The HCo(CO)₄ thus catalyzes the decomposition of the (SiH₃)₂NH first formed¹³.

B. By Covalant Halides

Although a number of covalent or semi-covalent halides have been found to readily cleave the Si—Co bond, it is interesting to find that some such compounds do not attack the bond at all. In those cases where no reaction occurs, it is not clear whether the lack of reactivity is due to thermodynamic or kinetic factors. From the electronegativity data given in Section IV, A, it seems likely that the polarity of the silicon-transition metal bond might be small. This could reduce the ease of nucleophilic attack at silicon in a rate-controlling step. However, it is likely that the rate-controlling step for many reactions might involve electrophilic attack at the transition metal.

It has been observed that mercuric iodide reacts reversibly with H_3Si — $Co(CO)_4$, *viz.*³,

 $2H_3Si-Co(CO)_4 + HgI_2 \rightleftharpoons 2SiH_3I + Hg[Co(CO)_4]_2$

however, no reaction occurred between mercuric iodide and F_3Si —Co(CO)₄ even after heating to 60° ⁸. When mercuric chloride, on the other hand, was heated with F_3Si —Co(CO)₄ for three hours at 60°, an analogous reaction did take place and a 90 per cent yield of SiF₃Cl was obtained⁸.

Excess germanium tetrafluoride cleaves the Si—Co bond in Me₃Si— Co(CO)₄ after ten minutes at room temperature to give analytically pure F_3Ge —Co(CO)₄. Quantitative reaction took place according to the equation^{5,7}

$$Me_3Si-Co(CO)_4 + GeF_4 \rightarrow F_3Ge-Co(CO)_4 + Me_3SiF.$$

When Me₂AsCl was mixed with an excess of Me₃Si—Co(CO)₄ a rapid reaction took place even at low temperatures^{5,7}. A dark red colour developed at -23° and it is believed that at this temperature the following reaction occurred:

 Me_3Si — $Co(CO)_4 + Me_2AsCl \rightarrow Me_2As$ — $Co(CO)_4 + Me_3SiCl$ On warming to room temperature, CO was evolved and quantitative yields of analytically pure, polymeric $[Me_2As$ — $Co(CO)_3]_x$ were isolated, *viz.*,

$$xMe_2As - Co(CO)_4 \rightarrow [Me_2As - Co(CO)_3]_x + xCO$$

No reaction occurred between Me₃Si—Co(CO)₄ or MeSiH₂—Co(CO)₄ and excess boron trifluoride at room temperature^{5,7,21}. Similarly, after acetyl chloride and Me₃Si—Co(CO)₄ had been held at room temperature for thirty minutes, both materials were recovered essentially quantitatively⁷. When equimolar quantities of Me₃Si—Co(CO)₄, acetyl chloride and boron trichloride were held at room temperature for thirty minutes, no reaction was observed⁶⁴.

Surprisingly, very little reaction took place between Me₃Si—Co(CO)₄ and a large excess of phosphorus pentafluoride at an autogenous gas pressure of approximately 20 atm. during two hours at room temperature. Similarly no reaction occurred between Me₃Si—Co(CO)₄ and excess phosphorus trifluoride even when they were heated together at 100° for one hour⁷. Some thermal decomposition of the Me₃Si—Co(CO)₄ took place during this period as expected, but most of the phosphorus trifluoride was recovered unchanged. No reaction took place between MeSiH₂—Co(CO)₄ and phosphorus trifluoride during one hour at room temperature²¹. When a solution of Me₃Si—Mn(CO)₅ and phosphorus trifluoride in pentane was simultaneously heated to approximately 100° for thirty minutes and exposed to ultraviolet radiation, essentially no cleavage of the Si—Mn bond was observed¹⁴.

A most unexpected and interesting reaction occurred between $MeSiH_2$ — $Co(CO)_4$ and phosphorus pentafluoride in which a net transfer of hydrogen from silicon to cobalt took place^{21,65}. Reaction commenced below 0° and was complete after three hours at room temperature. The chief products were: $MeSiF_2$ — $Co(CO)_4$, $MeSiF_2H$, $HCo(CO)_3(PF_3)$, $HCo(CO)_2(PF_3)_2$ and HCo(CO) (PF₃)₃. Exactly the same products were obtained by co-condensing an approximately equimolar mixture of $MeSiH_3$ and phosphorus pentafluoride on to $Co_2(CO)_8$ and allowing them to stand at room temperature for two and a half hours^{21,65}

Since there is no reaction between Me_3Si — $Co(CO)_4$ and phosphorus pentafluoride or between $MeSiH_2$ — $Co(CO)_4$ and phosphorus trifluoride, it appears that a key step in the reaction must have involved reduction of phosphorus pentafluoride by Si—H bonds. Some background experiments were therefore carried out in order to better understand this reaction. After ninety minutes at room temperature, approximately equimolar quantities of $MeSiH_3$ and phosphorus pentafluoride underwent the following reaction^{21,65}:

$$MeSiH_3 + PF_5 \rightarrow MeSiF_2H + PF_3 + H_2.$$

In a somewhat analogous reaction it was found that MeSiH₂Cl and phosphorus pentafluoride yielded, after one hour at room temperature, MeSiF₂H, phosphorus trifluoride and hydrogen chloride, viz.^{21,65},

$$MeSiH_2Cl + PF_5 \rightarrow MeSiF_2H + PF_3 + HCl.$$

Since the - Cl and - Co(CO)₄ groupings have a number of properties in common, it is believed that the MeSiH₂-Co(CO)₄ probably reacts initially in an exactly analogous fashion to MeSiH₂Cl, *viz.*,

 $MeSiH_2 - Co(CO)_4 + PF_5 \rightarrow MeSiF_2H + PF_3 + HCo(CO)_4$

Since it is known that Si—H bonds react readily with $HCo(CO)_4$ it seems likely that the following reaction would then occur:

 $MeSiF_2H + HCo(CO)_4 \rightarrow MeSiF_2-Co(CO)_4 + H_2.$

Also, since it is known that $HCo(CO)_4$ and phosphorus trifluoride react rapidly at low temperatures to give $HCo(CO)_x(PF_3)_{4-x}^{66}$ it seems that some of the $HCo(CO)_4$ could also react with the phosphorus trifluoride produced to give those carbonyl hydride species which were obtained in the original reaction between $MeSiH_2$ — $Co(CO)_4$ and phosphorus pentafluoride. It seems very probable that the net transfer of hydrogen from silicon to cobalt may occur via this reaction sequence.

C. By Tertiary Amines

The reactions described in this section may be regarded either as addition reactions to silicon or as reactions involving cleavage of the covalent silicontransition metal bond.

When H_3Si — $Co(CO)_4$ is treated either with trimethylamine or with pyridine, no carbon monoxide displacement is observed; instead the solid adducts, $SiH_3Co(CO)_4$. 2Base are obtained¹². Analogous adducts have been obtained from Me_3Si — $Co(CO)_4$ and trimethylamine or pyridine except that in this case the species formed have the composition Me_3SiCo $(CO)_4$. $Base^{64}$. The CO stretching vibrations for H_3Si — $Co(CO)_4$ and Me_3Si — $Co(CO)_4$ fall in the 2000–2130 cm⁻¹ range, whereas in the corresponding adducts they fall between 1870 and 1890 cm⁻¹. Since the $Co(CO)_4^{-1}$ ion exhibits its chief CO stretching vibration at 1883 cm^{-1 67}, it seems likely that these compounds are ionic compounds which could be formulated as $[(SiH_3 . 2B)]^+[Co(CO)_4]^-$ and $[(Me_3Si . B)]^+[Co(CO)_4]^-$. The latter species may therefore be regarded as the silicon-substituted quaternary

ammonium salt, e.g. $[Me_3NSiMe_3]^+[Co(CO)_4]^-$. An analogous compound has been reported for $H_3Si-Mn(CO)_5$, *i.e.* $[(SiH_3 . 2B)]^+[Mn(CO)_5]^{-12}$. It is interesting to find that $(H_3Si)_2Fe(CO)_4$ forms only the 1:2 adduct, $(H_3Si)_2Fe(CO)_4 . 2NMe_3$, even with a large excess of trimethylamine¹⁷. Infrared studies suggest that it is only partly ionic in nature and its chemical properties suggest that one trimethylamine molecule is coordinated to each SiH₃ group¹⁷.

These ionic, or partly ionic compounds, appear to be more chemically reactive than the parent compounds. Thus, although hydrogen chloride does not cleave the Si—Mn bond in H₃Si—Mn(CO)₅, even on warming, it reacts rapidly at -80° with the pyridine adduct, *viz.*¹³,

 $H_3Si - Mn(CO)_5.2py + 3HCl \rightarrow SiH_3Cl + HMn(CO)_5 + 2C_5H_5N.HCl$

Analogously, when $[(Me_3SiNMe_3)]^+[Co(CO)_4]^-$ was exposed to dry oxygen at one atm. pressure, an explosion occurred and 85 per cent of the Me_3Si- groups were recovered as $(Me_3Si)_2O^{64}$. This should be compared with the reaction of Me_3Si—Co(CO)_4 with oxygen (Section VI) in which a much less vigorous reaction was observed⁶⁴. When $[Me_3SiNMe_3]^+$ $[Co(CO)_4]^-$ was heated at 80° for 14 hours *in vacuo*, non-volatile, unidentified species were found together with trace amounts of $(Me_3Si)_2O$, trimethylamine and carbon monoxide⁶⁴. When excess gaseous hydrogen chloride was permitted to react with $(H_3Si)_2Fe(CO)_4$. 2NMe_3, it was found that $H_2Fe(CO)_4$, but no $H_3Si(H)Fe(CO)_4$ was produced¹⁷.

D. Insertion Reactions

It is well known that carbon monoxide will readily insert into carbontransition metal bonds⁶⁸ under relatively mild reaction conditions, *e.g.*,

$$Me-Mn(CO)_5 + CO \rightarrow MeCOMn(CO)_5$$

Sulphur dioxide undergoes an analogous type of reaction. With $MeMn(CO)_5$, for example, reaction occurs at -75° during one hour⁶⁹:

$$MeMn(CO)_5 + SO_2 \rightarrow MeSO_2Mn(CO)_5.$$

Silicon-transition metal carbonyls however, show no tendency to undergo these types of reactions^{4,14}. Neither H₃Si—Co(CO)₄ nor H₃Si—Mn(CO)₅ undergo direct carbonyl insertion into the Si-transition metal bond, even with high pressures of carbon monoxide¹³. Likewise, when Me₃Si—Mn(CO)₅ was held either at room temperature for forty hours, or at 100° for two and a half hours in the presence of liquid sulphur dioxide, no major reaction occurred, 75 per cent of the Me₃Si—Mn(CO)₅ being recovered in the former experiment and 89 per cent in the latter. No SO₂- insertion product was observed¹⁴. It has been suggested that the reluctance of the Si-transition metal bond to undergo insertion reactions may be related to the $(d \rightarrow d)\pi$ Si-metal interaction energy which would thereby be lost¹³.

VIII. SUBSTITUTION REACTIONS AT SILICON

Very little is known about substitution reactions at silicon during which the silicon-transition metal bond remains intact. However, a remarkable reaction occurs slowly in the gas phase at 75° between H₃Si—Mn(CO)₅ and hydrogen chloride in which substitution of hydrogen by chlorine occurs, *viz.*,

 $H_3Si-Mn(CO)_5 + xHCl \rightarrow SiH_{3-x}Cl_x-Mn(CO)_5 + xH_2$

where x = 1-3. No cleavage of the Si—Mn bond occurs during this process¹³.

IX. SUBSTITUTION REACTIONS AT THE TRANSITION METAL

Several reactions have been reported in which a CO group in the metal carbonyl portion of the molecule is replaced by a phosphine. The CO grouping is eliminated as carbon monoxide and no evidence has yet been obtained for its insertion into the silicon-transition metal bond as is frequently found with carbon transition metal carbonyls, *e.g.*⁷⁰,

 $MeMn(CO)_5 + Ph_3P \rightarrow MeCOMn(CO)_4(PPh_3).$

When R_3Si — $Co(CO)_4$ is permitted to react with triphenylphosphine or triethylphosphine, substitution occurs at room temperature, *viz.*,

$$R_3Si-Co(CO)_4 + R'_3P \rightarrow R_3Si-Co(CO)_3(PR'_3) + CO$$

where R = H and $R' = Ph^{13}$ and where R = Et or Cl and $R' = Et^{19}$. The Et₃P group enters into the position *trans* to the R₃Si- group¹⁹.

Ultraviolet irradiation of Me₃Si—Fe(CO)₂(π -C₅H₅) in the presence of Ph₂PCH₂CH₂PPh₂ or *cis*-Ph₂PCH=CHPPh₂ results in the formation of Me₃SiFe(diphos) (π -C₅H₅)⁷¹.

It was interesting to find that when a pentane solution containing equimolar quantities of Me₃Si—Mn(CO)₅ and trifluorophosphine was exposed to ultraviolet radiation for thirty minutes at approximately 100° essentially no cleavage of the Si—Mn bond occurred. Instead, a 90 per cent yield of Me₃Si—Mn(CO)₄(PF₃) was obtained together with small amounts of more highly PF₃-substituted products. The material consisted of the *trans* isomer only¹⁴.

X. CONCLUSIONS

In conclusion, it can clearly be seen, even from the small amount of information presently available, that the chemistries of compounds containing Si—Co, Si—Mn and Si—Fe bonds differ considerably from each other in certain respects. Broadly speaking, it appears that the order of increasing thermal stability is Si—Co < Si—Mn \leq Si—Fe and that the order of decreasing chemical reactivity is Si—Co > Si—Mn \geq Si—Fe.

It is likely that the most significant advances, in so far as understanding factors which control silicon-transition metal chemistry, will result from (i) a study of analogous carbon, silicon, germanium, tin and lead compounds element-transition metal bond. containing Group IV e.g., а Me_3M —Co(CO)₄, (M = C, Si, Ge, Sn, Pb) and (ii) a study of similar types of compounds, e.g., Me₃Si-Co(CO)₄ and Me₃Si-Mn(CO)₅ containing silicon joined to different transition elements. A really meaningful interpretation of the data from studies of type (ii) can, of course, only be presented when comparisons are also made with analogous carbon, germanium, tin and lead compounds.

The number and variety of possible compounds containing even one given silicon-transition metal bond which could be synthesized is already very large. Considering presently known techniques only, one can synthesize compounds having different substituents on the silicon or different substituents, such as CO, phosphines, π - bonded organic groups, etc., on the transition metal. When changes in substituents are then extended to species containing more than one silicon-transition metal bond or to polynuclear species, a number of which are already known, an enormous range of compounds is presented.

It seems very likely that in a relatively few years, the chemistry of compounds containing silicon joined to any one particular transition metal will be as extensive as the chemistry of, for example, compounds containing Si—N bonds. Furthermore, it seems highly probable that the chemistries of classes of compounds containing silicon joined to different transition metals may differ from each other to the extent to which compounds containing Si-O and Si-N bonds, for example, differ from each other.

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Notes added in proof.

- 1. The conclusions reached in the following discussion would remain unchanged even if it were assumed that that the effective steric repuirements of the axially-located groups were such that the equatorial carbonyl groups were, from steric requirements alone, approximately coplanar with the central transition element. In this case, a would simply be close to zero.
- 2. Since this manuscript was submitted for publication, it has been reported⁷³ that the Si—Co—CO_{eg}, angle, determined on a gaseous sample of H_3Si —Co(CO)₄, (electron diffraction) is 81.7°. Distortions are therefore probably not determined chiefly by crystal lattice effects.